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| Objective |
| Batch name: Process template |
| This process is a guideline on how to spin coat, develop and rinse CSAR62 on substrates as Si, SiO2, III-Vs, and SOI.  CSAR is a positive e-beam resist chemically the same as ZEP, but with a slightly different dose to clear. |

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| Step Heading | Equipment |  | Comments |
| 1. Pretreatment | | |  |
| * 1. Surface treatment | BHF dip  *or*  HMDS | BHF dip for Si substrates (30 sec, H2O 5 min)  HMDS treatment for SiO2 and III-V substrates | Generally, pre-treatment is not recommended. |
| 1. Spin coat of CSAR | | |  |
| * 1. Coat wafers | Spin coater | **Resist:** CSAR (AR-P 6200, AllResist)  **Spin:** 60 sec @ 4000 rpm (for appr. 180 nm)  **Softbake:** 1 min @ 180 oC | Use syringe with filter or disposable pipette (cleaned by N2 gun). Soft bake is not a crucial step according to AllResist |
| 1. E-beam exposure | | |  |
| * 1. E-beam exposure | E-beam writer | Dose: 250 - 350 µC/cm2; a dose-test is required. | Dose depends strongly on substrate material, thickness of resist, critical dimension, load of pattern, and developer type and time. |
| 1. Development & Rinse | | |  |
| * 1. Develop-ment | Petribowl, fumehood | Develop with AR 600-546, 60 sec  Rinse in IPA, 60 sec  blow dry with N2 |  |
| 1. Pattern transfer | | |  |
| Please insert which steps you wish to perform after development (e.g. metallization or dry etch). | | |  |
| 1. Lift-off and Strip | | |  |
| * 1. Lift-off | Petribowl, fumehood in D-3 | Remover AR 600-71  USE REMOVER AR 600-71 ONLY AT ROOM TEMPERATURE.  Rinse with IPA. | **For lift-off of metal:** Leave the wafer or chip in remover AR 600-71 for 1-2 hours; this normally lifts greater parts of the metal. If this is not enough, use ultrasonic 10-20 seconds.  Metal deposited in Alcatel is slightly easier to lift than metal deposited in Wordentec. |